

# Ruslan Ivanov

## List of Publications by Citations

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papers

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ext. citations

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avg, IF

2.16

L-index

| #  | Paper  | IF  | Citations |
|----|--|-----|-----------|
| 12 | Highly polarized photoluminescence and its dynamics in semipolar (202 $\bar{1}$ 1) InGaN/GaN quantum well. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 111113  | 3.4 | 29        |
| 11 | High spatial uniformity of photoluminescence spectra in semipolar (202 $\bar{1}$ 1) plane InGaN/GaN quantum wells. <i>Journal of Applied Physics</i> , <b>2015</b> , 117, 023111   | 2.5 | 25        |
| 10 | Impact of carrier localization on radiative recombination times in semipolar (202 $\bar{1}$ 1) plane InGaN/GaN quantum wells. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 211109   | 3.4 | 20        |
| 9  | Scanning near-field microscopy of carrier lifetimes in m-plane InGaN quantum wells. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 031109   | 3.4 | 12        |
| 8  | Polarization-Resolved Near-Field Spectroscopy of Localized States in m-Plane In <sub>x</sub> Ga <sub>1-x</sub> N/GaN Quantum Wells. <i>Physical Review Applied</i> , <b>2017</b> , 7,  | 4.3 | 12        |
| 7  | Direct Measurement of Nanoscale Lateral Carrier Diffusion: Toward Scanning Diffusion Microscopy. <i>ACS Photonics</i> , <b>2018</b> , 5, 528-534   | 6.3 | 12        |
| 6  | Influence of well width fluctuations on recombination properties in semipolar InGaN quantum wells studied by time- and spatially-resolved near-field photoluminescence. <i>Optical Materials Express</i> , <b>2017</b> , 7, 3116                           | 2.6 | 10        |
| 5  | Properties of near-field photoluminescence in green emitting single and multiple semipolar (202 $\bar{1}$ 1) plane InGaN/GaN quantum wells. <i>Optical Materials Express</i> , <b>2016</b> , 6, 39   | 2.6 | 5         |
| 4  | Influence of shallow versus deep etching on dark current and quantum efficiency in InAs/GaSb superlattice photodetectors and focal plane arrays for long wavelength infrared detection. <i>Infrared Physics and Technology</i> , <b>2018</b> , 95, 158-163 | 2.7 | 5         |
| 3  | LWIR QWIPs at IRnova for next generation polarimetric imaging. <i>Infrared Physics and Technology</i> , <b>2018</b> , 95, 177-182  | 2.7 | 3         |
| 2  | T2SL development for space at IRnova: from eSWIR to VLWIR <b>2019</b> ,  |     | 2         |
| 1  | QWIPs are keeping their promises <b>2019</b> ,   |     | 1         |